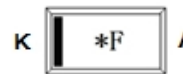


WSB5556Z
Schottky Barrier Diode
[Http://www.sh-willsemi.com](http://www.sh-willsemi.com)
Features

- 100mA Average rectified forward current
- Low forward voltage
- Low leakage current
- Small package DFN0603-2L


DFN0603-2L(Bottom View)

Circuit

Marking
Applications

- Low Current rectification

Absolute maximum ratings

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	V_{RM}	30	V
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_O	100	mA
Peak forward surge current (8.3ms single sine pluse)	I_{FSM}	2	A
Junction temperature	T_J	150	°C
Operating temperature	T_{opr}	-40 ~ 150	°C
Storage temperature	T_{stg}	-40 ~ 150	°C

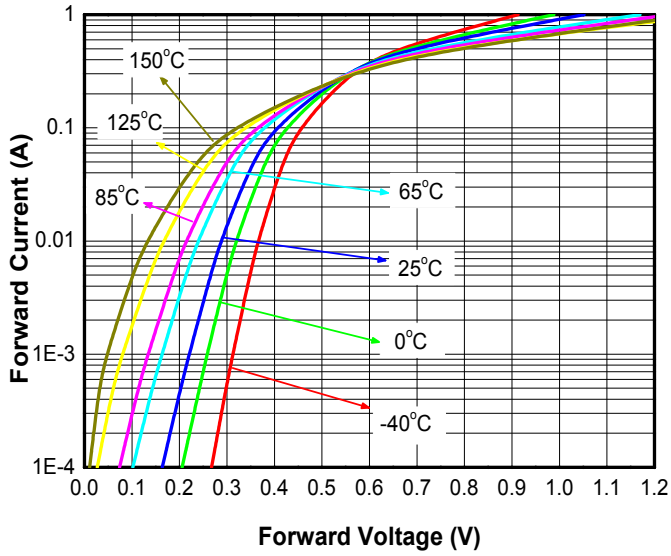
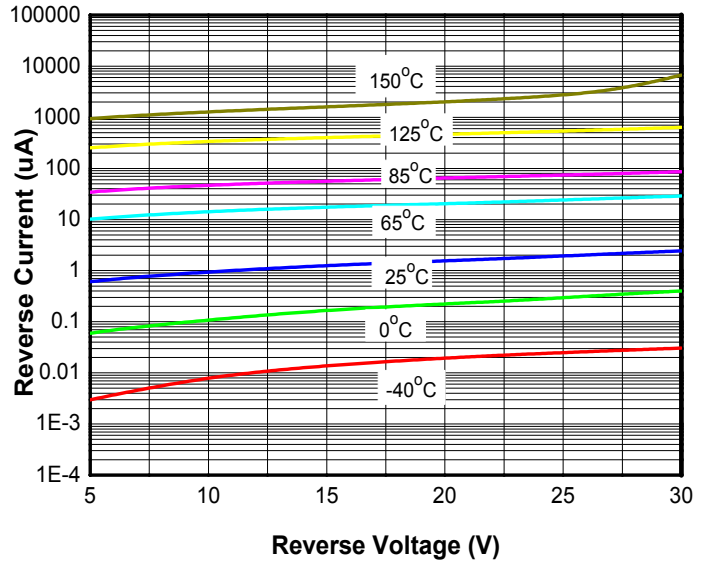
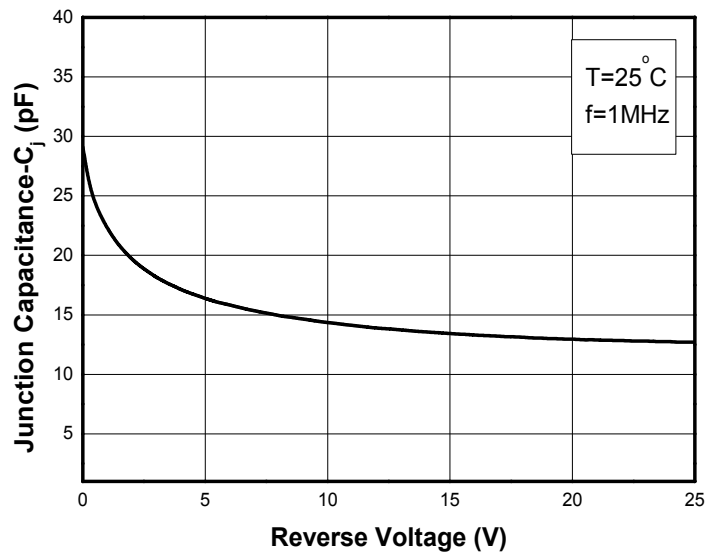
Electronics characteristics ($T_A=25^\circ\text{C}$)

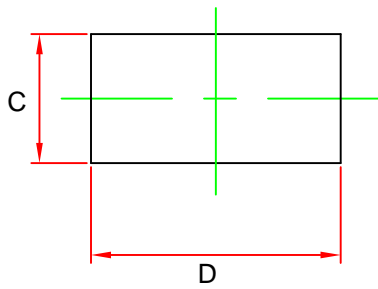
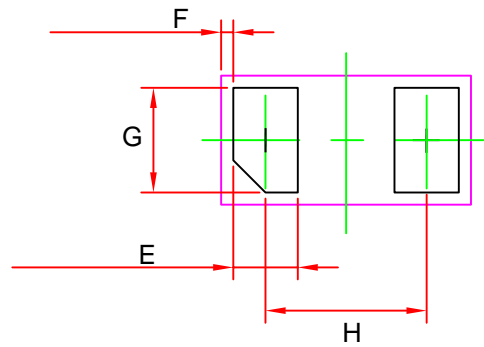
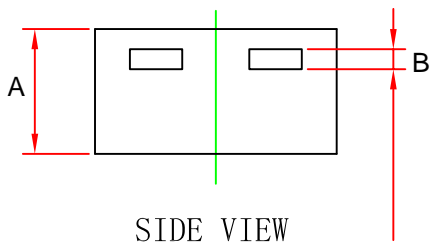
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Voltage	V_R	$I_R=100\mu\text{A}$	30			V
Forward Voltage	V_F	$I_F=1\text{mA}$			0.28	V
		$I_F=10\text{mA}$			0.36	V
Reverse current	I_R	$V_R=10\text{V}$			6	μA
		$V_R=30\text{V}$			15	μA
Junction capacitance	C_J	$V_R=5\text{V}, F=1\text{MHz}$		16		pF
Thermal Resistance	$R_{\theta(JA)}$	Junction to Ambient			650	K/W

Order Information

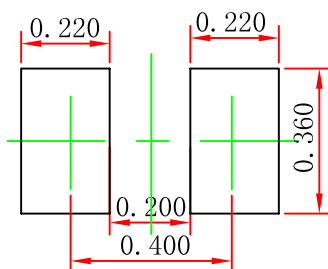
Device	Package	Marking	Shipping
WSB5556Z-2/TR	DFN0603-2L	*F ⁽¹⁾	10000/Reel&Tape

Note 1: * = Month code(A~Z); F = Device code;

Typical characteristics (Ta=25°C, unless otherwise noted)

Fig.1 Forward voltage vs. Forward current

Fig.2 Reverse current vs. Reverse voltage

Fig.3 Junction capacitance vs. Reverse voltage

Package outline dimensions

TOP VIEW

BOTTOM VIEW

SIDE VIEW

Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.275	0.310	0.340
B	0.050 REF.		
C	0.270	0.320	0.370
D	0.570	0.620	0.670
E	0.125	0.160	0.195
F	0.030 REF.		
G	0.225	0.260	0.295
H	0.365	0.400	0.435

**Recommend land pattern
(Unit: mm)**

Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.